

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-20	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Drain Current (Note 6) Continuous	I <sub>D</sub>	T <sub>A</sub> = +25°C -4.6	A
		T <sub>A</sub> = +70°C -3.7	
Pulsed Drain Current (Note 7)	I <sub>DM</sub>	-18	A
Body-Diode Continuous Current (Note 6)	I <sub>S</sub>	2.0	A

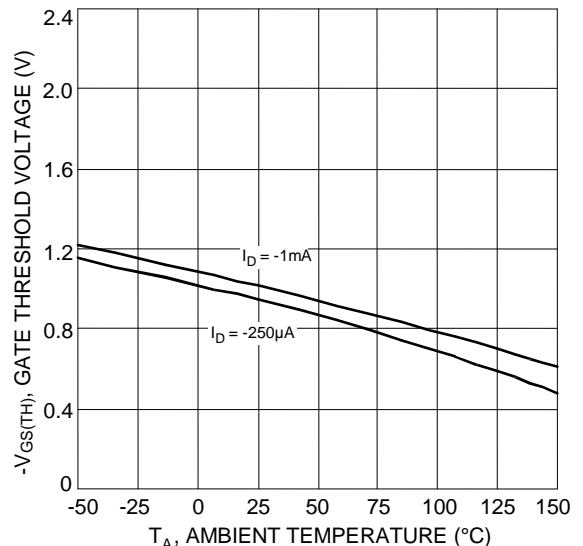
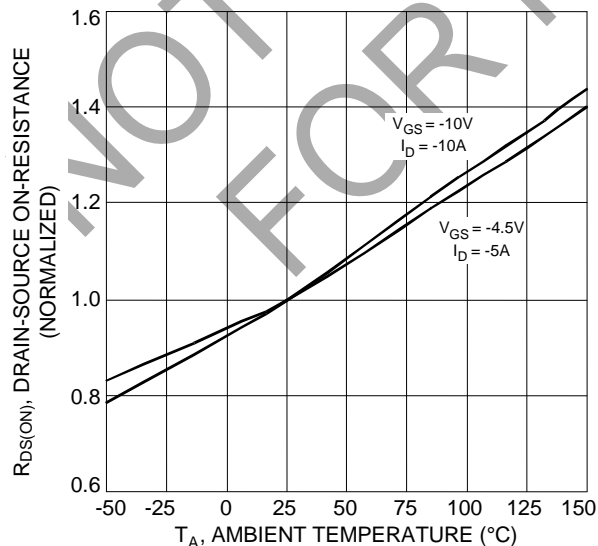
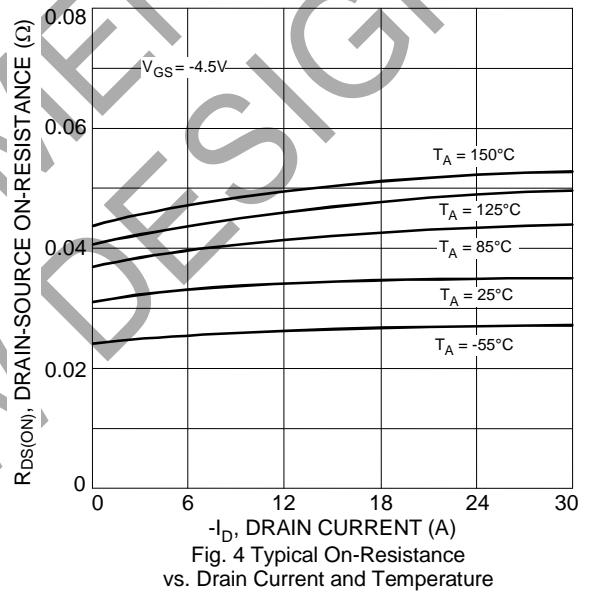
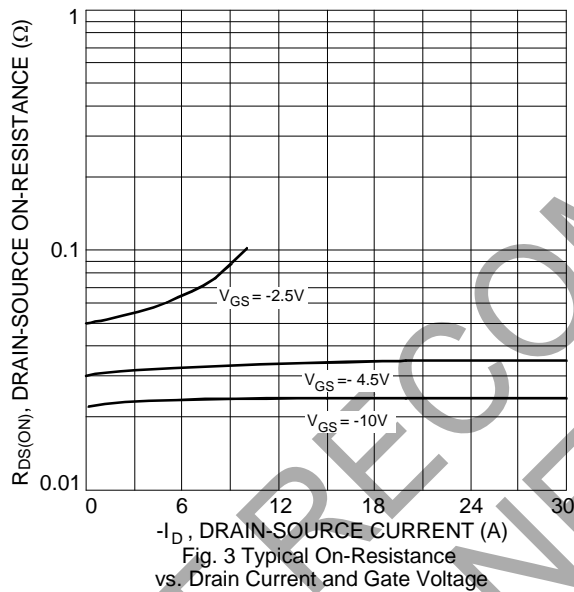
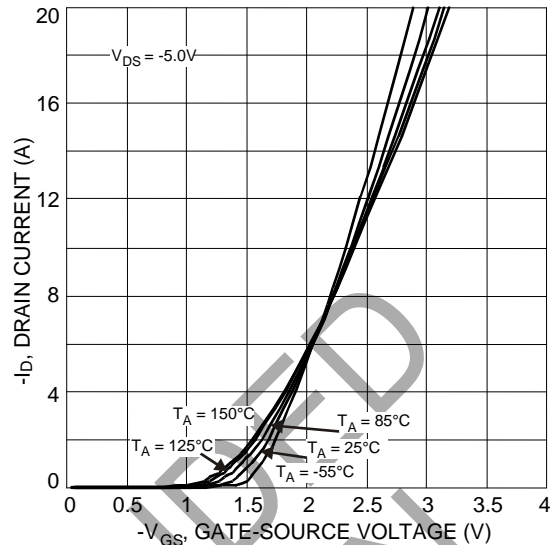
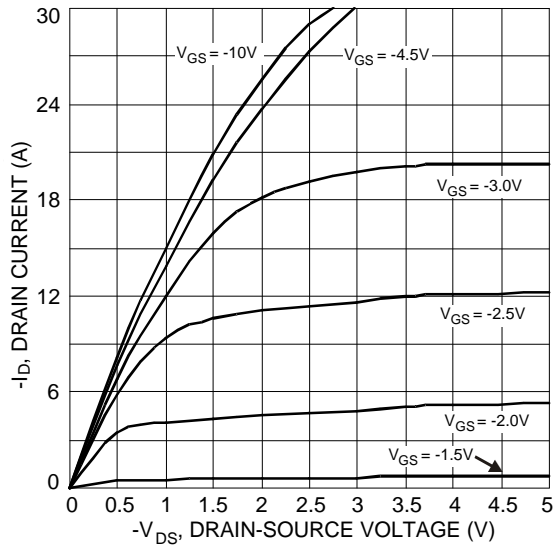
## Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P <sub>D</sub>	1.25	W
Thermal Resistance, Junction to Ambient (Note 6); Steady-State	R <sub>θJA</sub>	100	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>STATIC PARAMETERS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	I <sub>D</sub> = -250μA, V <sub>GS</sub> = 0V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	μA	T <sub>J</sub> = +25°C, V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Body Leakage Current	I <sub>GSS</sub>	—	—	±100	nA	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±12V
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.6	-0.96	-1.2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
On State Drain Current (Note 8)	I <sub>D(ON)</sub>	-15	—	—	A	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -5V
Static Drain-Source On-Resistance (Note 8)	R <sub>DS(ON)</sub>	—	29 55	40 70	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -4.6A V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -3.8A
Forward Transconductance (Note 8)	g <sub>FS</sub>	—	9	—	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -4.6A
Diode Forward Voltage (Note 8)	V <sub>SD</sub>	-0.5	-0.72	-1.4	V	I <sub>S</sub> = -2.1A, V <sub>GS</sub> = 0V
Maximum Body-Diode Continuous Current (Note 6)	I <sub>S</sub>	—	—	-1.7	A	—
<b>DYNAMIC PARAMETERS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	820	—	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	200	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	160	—	pF	
Gate Resistance	R <sub>G</sub>	—	2.5	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V f = 1.0MHz
<b>SWITCHING CHARACTERISTICS</b>						
Total Gate Charge	Q <sub>G</sub>	—	10.1	—	nC	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -4.5A
Gate-Source Charge	Q <sub>GS</sub>	—	1.5	—		
Gate-Drain Charge	Q <sub>GD</sub>	—	4.3	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	4.4	—	ns	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -1A, R <sub>G</sub> = 6.0Ω
Rise Time	t <sub>r</sub>	—	9.9	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	28.0	—		
Fall Time	t <sub>f</sub>	—	23.4	—	—	—

- Notes:
- Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width t ≤ 10s.
  - Repetitive Rating, pulse width limited by junction temperature.
  - Test pulse width t = 300μs.
  - Guaranteed by design. Not subject to production testing.



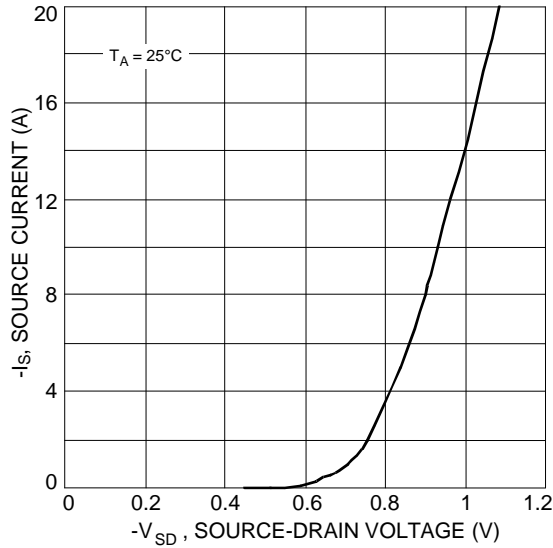


Fig. 7 Diode Forward Voltage vs. Current

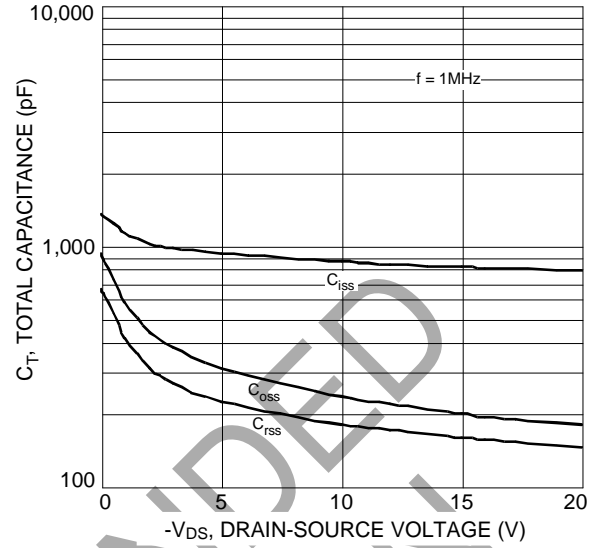


Fig. 8 Typical Total Capacitance

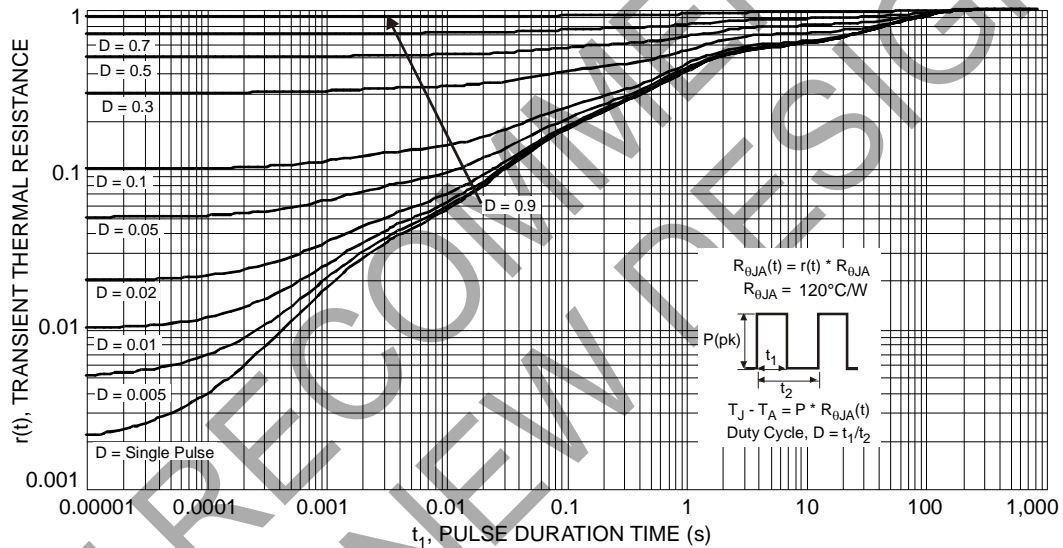
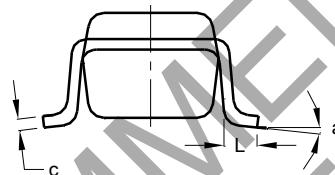
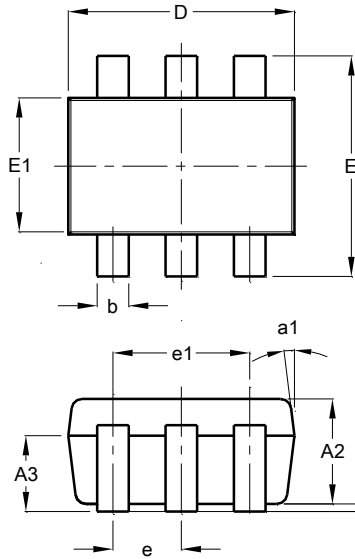


Fig. 9 Transient Thermal Response

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT26

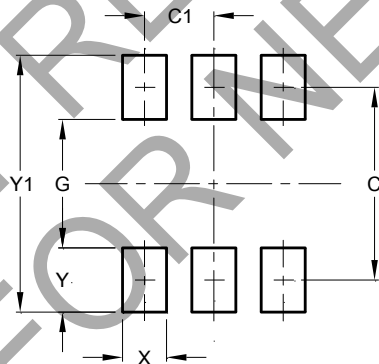


SOT26			
Dim	Min	Max	Typ
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	-	-	0.95
e1	-	-	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	-	-	8°
a1	-	-	7°
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT26



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20

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